

UNISONIC TECHNOLOGIES CO., LTD

UH11K

Preliminary

NPN EPITAXIAL SILICON TRANSISTOR

DUAL BIAS RESISTOR TRANSISTORS

DESCRIPTION

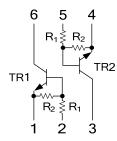
The UTC UH11K is a dual bias resistor transistors, it uses UTC's advanced technology to provide customers with saving board space, reducing component count, etc.

The UTC UH11K is suitable for low power surface mount applications, etc.

FEATURES

- * Reducing component count
- * Saving board space

EQUIVALENT CIRCUIT



ORDERING INFORMATION

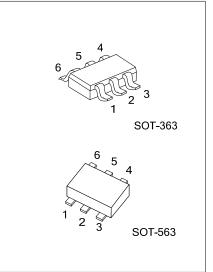
Ordering Number	Deekege	Pin Assignment						Deaking	
Ordering Number	Package	1	2	3	4	5	6	Packing	
UH11KG-AL6-R	SOT-363	E1	B1	C2	E2	B2	C1	Tape Reel	
UH11KG-AN6-R	SOT-563	E1	B1	C2	E2	B2	C1	Tape Reel	
Noto: Din Assignment: E: Emitter D: Base	C: Collector								

Note: Pin Assignment: E: Emitter B: Base C: Collector

UH11KG- <u>AL6-R</u>	(1)Packing Type (2)Package Type (3)Green Package	 (1) R: Tape Reel (2) AL6: SOT-363, AN6: SOT-563 (3) G: Halogen Free and Lead Free 	
	(3)Green Package	(3) G: Halogen Free and Lead Free	

MARKING

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SOT-363	SOT-563				
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■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V _{CBO}	50	V
Collector-Emitter Voltage		V _{CEO}	50	V
Collector Current		Ιc	100	mA
Power Dissipation	SOT-363	Р	150	mW
	SOT-563	P _D	120	mW
Junction Temperature		TJ	-55 ~ +150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

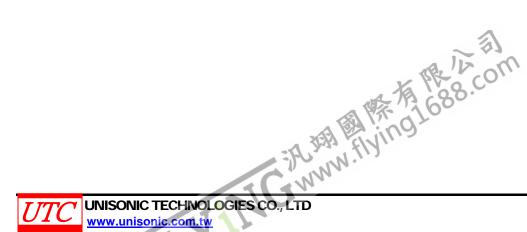
Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
OFF CHARACTERISTICS								
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =10μΑ, I _E =0	50			V		
Collector-Emitter Breakdown Voltage (Note 1)	BV _{CEO}	I _C =2.0mA, I _B =0	50			V		
Collector-Base Cutoff Current	I _{CBO}	V _{CB} =50V, I _E =0			100	nA		
Collector-Emitter Cutoff Current	I _{CEO}	V _{CE} =50V, I _B =0			500	nA		
Emitter-Base Cutoff Current	I _{EBO}	V _{EB} =6.0V, I _C =0			0.5	mA		
ON CHARACTERISTICS (Note 2)								
DC Current Gain	h _{FE}	V _{CE} =10V, I _C =5.0mA	35	60				
Output Voltage (on)	V _{OL}	V_{CC} =5.0V, V_{B} =2.5V, R_{L} =1.0 k Ω			0.2	V		
ON CHARACTERISTICS (Note 2)								
Input Resistor	R ₁		7.0	10	13	kΩ		
Resistor Ratio	R_1/R_2		0.8	1.0	1.2	kΩ		

Notes: 1. Pulse Test: Pulse Width<300µs, Duty Cycle<2.0%

2. Pulse Test: Pulse Width<300ms, Duty Cycle<2.0%



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